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In the Claims:**Claim 1 (currently amended):** A structure comprising:

a first conductor situated in a semiconductor die, said first conductor comprising interconnect metal;

a first isolation layer situated over said first conductor;

a second conductor comprising at least two conductor segments situated over said first isolation layer, said second conductor comprising under bump metal, said second conductor having at least one external pad associated with one of said at least two conductor segments, wherein said first conductor electrically connects said at least two conductor segments;

a second isolation layer situated over said second conductor, said second isolation layer having at least one hole over said at least one external pad of said second conductor;

a bump attach site located at said at least one hole over said at least one external pad.

Claim 2 (original): The structure of claim 1 wherein said under bump metal comprises material selected from the group consisting of copper and aluminum.

Claim 3 (original): The structure of claim 1 wherein said first conductor is between approximately 2.0 microns and 5.0 microns thick.

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Claim 4 (original): The structure of claim 1 wherein said first isolation layer comprises at least one via.

Claim 5 (original): The structure of claim 4 wherein said first conductor is connected to said second conductor through said at least one via so as to form an inductor.

Claim 6 (canceled).

Claim 7 (currently amended): The structure of claim 6 wherein said interconnect metal comprises material selected from the group consisting of copper and aluminum.

Claim 8 (original): The structure of claim 7 wherein said first conductor is between approximately 1.0 micron and approximately 2.0 microns thick.

Claim 9 (previously presented): The structure of claim 1 wherein said second conductor is patterned from a layer of under bump metal.

Claim 10 (original): The structure of claim 9 wherein said layer of under bump

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material comprises material selected from the group consisting of copper and aluminum.

Claim 11 (previously presented): The structure of claim 10 wherein said second conductor is between approximately 2.0 microns and approximately 5.0 microns thick.

Claim 12 (original): The structure of claim 11 wherein said first and said second isolation layers comprise a dielectric.

Claim 13 (original): The structure of claim 12 wherein said dielectric comprises a material selected from the group consisting of BCB and polyimide.

Claim 14 (original): The structure of claim 12 wherein each of said first and said second isolation layers is between approximately 5.0 microns and approximately 10.0 microns thick.

Claim 15 (original): The structure of claim 1 wherein said second conductor is situated substantially directly above said first conductor.

Claim 16 (original): The structure of claim 15 wherein said first and said second conductors are cross-coupled so as to form a transformer.

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Claim 17 (currently amended): A method for realizing passives, said method comprising steps of:

fabricating a first conductor in a semiconductor die, said first conductor comprising interconnect metal;

forming a first isolation layer over said first conductor;

fabricating a second conductor comprising at least two conductor segments over said first isolation layer, said second conductor comprising under bump metal, said second conductor having at least one external pad associated with one of said at least two conductor segments, wherein said first conductor electrically connects said at least two conductor segments;

forming a second isolation layer over said second conductor, said second isolation layer having at least one hole over said at least one external pad of said second conductor;

fabricating a bump attach site at said at least one hole over said at least one external pad.

Claim 18 (original): The method of claim 17 wherein said under bump metal comprises material selected from the group consisting of copper and aluminum.

Claim 19 (original): The method of claim 17 wherein said first conductor is between approximately 2.0 microns and 5.0 microns thick.

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Claim 20 (original): The method of claim 17 further comprising a step of fabricating at least one via in said first isolation layer prior to said step of depositing said second isolation layer.

Claim 21 (original): The method of claim 20 further comprising a step of connecting said first conductor to said second conductor through said at least one via so as to form an inductor.

Claim 22 (canceled).

Claim 23 (currently amended): The method of claim ~~22~~17 wherein said interconnect metal comprises material selected from the group consisting of copper and aluminum.

Claim 24 (original): The method of claim 23 wherein said first conductor is between approximately 1.0 micron and approximately 2.0 microns thick.

Claim 25 (previously presented): The method of claim 17 wherein said second conductor is patterned from a layer of under bump metal.

Claim 26 (original): The method of claim 25 wherein said layer of under bump

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metal comprises material selected from the group consisting of copper and aluminum.

Claim 27 (previously presented): The method of claim 26 wherein said second conductor is between approximately 2.0 microns and approximately 5.0 microns thick.

Claim 28 (original): The method of claim 27 wherein said first and said second isolation layers comprise a dielectric.

Claim 29 (original): The method of claim 28 wherein said dielectric comprises a material selected from the group consisting of BCB and polyimide.

Claim 30 (original): The method of claim 17 wherein each of said first and said second isolation layers is between approximately 5.0 microns and approximately 10.0 microns thick.

Claim 31 (original): The method of claim 17 wherein said second conductor is fabricated substantially directly above said first conductor.

Claim 32 (original): The structure of claim 31 wherein said first and said second conductors are cross-coupled so as to form a transformer.